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(54) **THICK SINGLE CRYSTAL DIAMOND LAYER METHOD FOR MAKING IT AND GEMSTONES PRODUCED FROM THE LAYER**

DICKE EINKRISTALLINE DIAMANTSCHICHT, VERFAHREN ZUR HERSTELLUNG DER SCHICHT UND EDELSTEINE HERGESTELLT DURCH BEARBEITUNG DER SCHICHT

COUCHE DE DIAMANT MONOCRISTALLIN EPAISSE, PROCEDE DE FABRICATION, ET PIERRES PRECIEUSES PRODUITES A PARTIR DE CETTE COUCHE

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- (56) References cited:
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Note: Within nine months from the publication of the mention of the grant of the European patent, any person may give notice to the European Patent Office of opposition to the European patent granted. Notice of opposition shall be filed in a written reasoned statement. It shall not be deemed to have been filed until the opposition fee has been paid. (Art. 99(1) European Patent Convention).

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